Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	88	(semiconductor adj layer).clm. and (gate adj electrode).clm. and (gate adj wiring).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 07:59
L2	20	(semiconductor adj layer).clm. and (gate adj electrode).clm. and (gate adj wiring).clm. and (conductive adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 07:59
L3	16	(semiconductor adj layer).clm. same (gate adj electrode).clm. and (gate adj wiring).clm. and (conductive adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:00
L4	9	(semiconductor adj layer).clm. same (gate adj electrode).clm. same (gate adj wiring).clm. and (conductive adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:00
L5	5	(semiconductor adj layer).clm. same (gate adj electrode).clm. same (gate adj wiring).clm. same (conductive adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:01
L6	4	(semiconductor adj layer).clm. same (gate adj electrode).clm. same (gate adj wiring).clm. same (conductive adj layer).clm. same channel.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:01
L7	2	(semiconductor adj layer).clm. with (gate adj electrode).clm. same (gate adj wiring).clm. same (conductive adj layer).clm. same channel.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:01
L8	0	(semiconductor adj layer).clm. with (gate adj electrode).clm. with (gate adj wiring).clm. same (conductive adj layer).clm. same channel.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:01